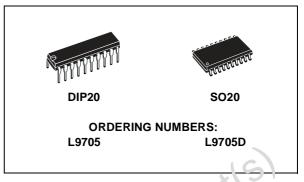


L9705

DOUBLE QUAD CONTACT INTERFACE CIRCUIT

- OPERATING DC SUPPLY VOLTAGE RANGE 5V TO 25V
- SUPPLY OVERVOLTAGE PULSE UP TO 40V
- VERY LOW STAND-BY QUIESCENT CURRENT, MAX 50µA
- INTERNAL CLAMPING DIODES AT CONTACT INPUTS TO Vs AND gnd WITH PULSE CURRENT CAPABILITY UP TO +50mA, -75mA
- CHIP ENABLE FUNCTION AND TRISTATE OUTPUTS FOR PARALLEL BUS CONNECTION
- NOMINAL CONTACT CURRENTS OF 10mA DEFINED WITH EXTERNAL CONTACT SERIES RESISTORS RIN1-8
- CONTACT STATUS MONITORING BY MEANS OF COMPARING THE RESISTANCE AT CONTACT SENSE INPUTS WITH THE INTERNAL REFERENCE RESISTOR VALUE
- RESISTANCE COMPARING WITH HYSTERESIS FOR HIGH NOISE IMMUNITY AND IMMUNITY TO GROUND AND BATTERY POTENTIAL DIFFERENCES

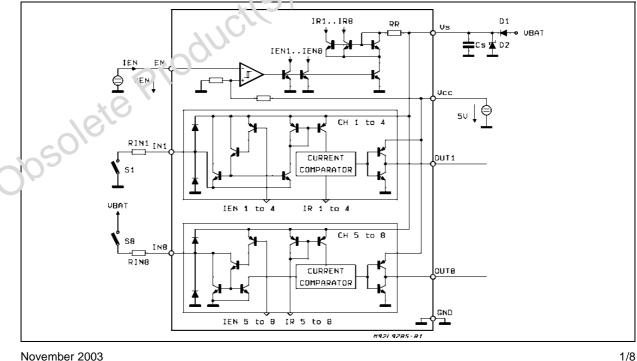
BLOCK DIAGRAM



DESCRIPTION

The L9705 is a bipolar monolitize integrated circuit for monitoring the status of up to four contacts connected to GND and up to jour contacts connected to the battery. The contact sense input supply the contact current and perform the contact resistance comparison function.

At the output the contact status is translated into a logical LOW level (contact closed) or logical HIGH l'evel (contact open).

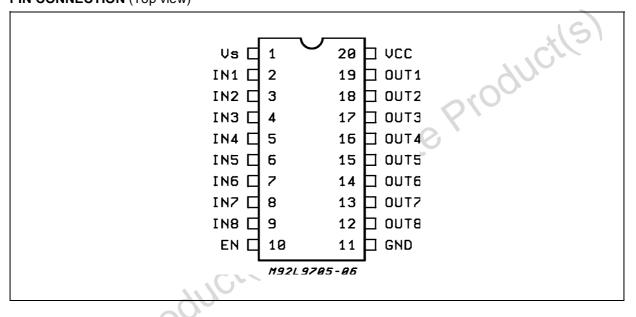


L9705

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{SDC}	DC Supply Voltage		+26	V
V _{SP}	Peak Transient Supply Voltage (t \leq 400ms)		+40	V
V _{CC}	Logic Supply Voltage		7	V
I _{INDC}	Input DC Current		±40	mA
I _{INP}	Input Pulse (t _p = 0 to 2ms; f≤ 0.2Hz; n = 25000)		-75 to 50	mA
lout	Output Current ($V_0 = 0$ to 5.5V)		internally limited	
V _{EN}	Enable Input Voltage		V _{CC} +0.3V;-0.3V	V
P _{tot}	Total Power Dissipation (T _{amb} = 80°C)	DIP 20 SO 20	875 420	mW mW
Тj	Junction Temperature Range		max 150	°C

PIN CONNECTION (Top view)



THERMAL DATA

Symbol	Parameter	DIP20	SO20	Unit
R _{th j-amb}	Thermal Resistance Junction to ambient	80	165	°C/W

ELECTRICAL CHARACTERISTCS

(V_S = 5 to 25V, V_{CC} = 4.75 to 5.25V, V_{bat} -0.5V < V_S ,< V_{bat} -1V , T_j = -40 to 150°C unless otherwise specified.)

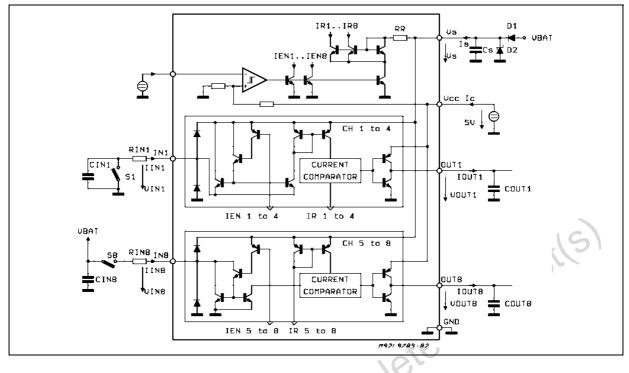
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
V _{ENL}	Enable Input Voltage LOW (device activated)		-0.3		0.8	V
V _{ENH}	Enable Input Voltage HIGH		2.4		V _{CC}	V
V_{ENh}	Enable Input Threshold Hysteresis		200	420	800	mV
I _{EN}	Enable Input Current	$\begin{array}{l} 2.4 V < V_{EN} < V_{CC} \\ 0 V < V_{EN} < 0.8 V \end{array}$	-5	-1	5	μΑ μΑ
Vouth	Output Voltage HIGH	0 < Ι _{Ουτ} < 100μΑ	4	V _{CC} - 0.1	Vcc	V
IOUT	Output Current	OUT status = HIGH; V _{OUT} = 0		0.5	2	mA
VOUTL	Output Voltage LOW	I _{OUT} = -1mA	0.05	0.2	0.4	V
IOUT	Output Current	OUT status = LOW; V _{OUT} = 5.5V		-5	-20	mA
IOUT TS	Output Tristate Current	0 < V _{OUT} < V _{CC}			0.5	μA
V _{IN 1,4}	Input Voltage (device active)	$EN = LOW; R_{IN} = 1K\Omega$	V _S - 2	V _S - 1.5	V _S - 0.4	D V
V _{IN 5,8}	Input Voltage (device active)	$EN = LOW; R_{IN} = 1K\Omega$	0.4	1.5	2	V
V _{IN}	Input VoltageDuring Clamp (device disabled)	EN = HIGH; I _{IN} = 30mA I _{IN} = -30mA	V _S +0.3 -2	Vs +1 -1	V _S +2 -0.3	V V
R _{IL 1,4}	Input Resistor LOW Threshold (note 1)	$5V < V_S < 16V; \Delta V_{GND} \le 0.1V_S$ $ \Delta V_{BAT} \le 0.1V_{BAT}$	1.8	4		KΩ
R _{IL 5,8}	Input Resistor LOW Threshold (note 1)	$5V < V_S < 16V; \Delta V_{GND} \le 0.1V_S$ $ \Delta V_{BAT} \le 0.1V_{BAT}$	1.8	4.8		KΩ
R _{IH 1,4}	Input Resistor HIGH Threshold (note 1)	$\begin{array}{l} 5V < V_S < 16V; \ \left \Delta V_{GND} \right \le 0.1V_S \\ \left \Delta V_{BAT} \right \le 0.1V_{BAT} \end{array}$		5.3	20	KΩ
R _{IH 5,8}	Input Resistor HIGH Threshold (note 1)	$ \begin{array}{l} 5V < V_{S} < \!\! 16V; \ \left \Delta V_{GND} \right \! \leq \! 0.1 V_{S} \\ \left \Delta V_{BAT} \right \! \leq \! 0.1 V_{BAT} \end{array} $		6.5	29	KΩ
R _{IL}	Input Resistor Threshold Ratio (note 1)	$5V < V_S < 16V; \Delta V_{GND} \le 0.1V_S$ $ \Delta V_{BAT} \le 0.1V_{BAT}$	0.65	0.75	0.85	
R _{IH}	Input Resistor Threshold Ratio (note 1)	$5V < V_S < 16V; \Delta V_{GND} \le 0.1V_S$ $ \Delta V_{BAT} \le 0.1V_{BAT}$	0.65	0.75	0.85	
IQC	Quiescent Current	EN = HIGH (t _{ENH} >20μs) V _S = 5 to 16V; T _j = -40 to 85°C		20	40	μA
I _{QS}	Quiescent Current	all contact open			10	μA
IQS	Quiescent Current	all contact closed			35	μA
Σl _{IN} (2)	Quiescent Current	$ \Delta V_{BAT} \le 0.1 V_{BAT}$			25	μA
IQC	Quiescent Current	EN = LOW			5	mA
las	Quiescent Current	EN = LOW			8	mA
t _{do}	Delay Time/Output (EN LOW to Output Data Ready) (note 3)	C _{OUT} ≤ 50pF			15+ 3R _{IN} ∙CIN	μs
tats	Delay Time/Tristate (EN HIGH to Output Tristate) (note 3)	C _{OUT} ≤ 50pF			10	μs
	Delay Time Input-Output (note 3)	$EN = LOW; C_{OUT} \le 50pF$				

Notes: 1. The input resistor threshold value is a resistor value from the IN-pin to ground at which the corresponding output changes its status (fig.4)
2. Σl_{IN} is the sum of the IN5 to IN8 input currents.
3. The delay times are defined from the crossing point of 50% initiating signal amplitude to the crossing point of 50% output signal amplitude to the crossing point of 50% output signal amplitude.

amplitude



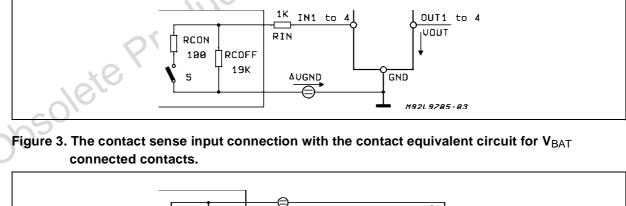
Figure 1. Typical application diagram for the L9705 circuit. The current flowing in the arrow direction is assumed positive. The external capacitors CIN and COUT represent the total wiring capacitance at the corresponding pins.

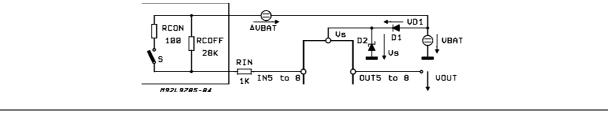


FUNCTIONAL DESCRIPTION

The L9705 circuit monitors the status of the contacts which are connected through the series external resistors R_{IN} to the contact sense input pins. The contacts equivalent circuit is supposed to be as shown in fig.2 for GND connected contacts (IN 1 to 4) and as shown in fig. 3 for V_{BAT} connected contacts (IN 5 to 8).

Figure 2. The contact sense input connection with the contact equivalent circuit for GND connected contacts.





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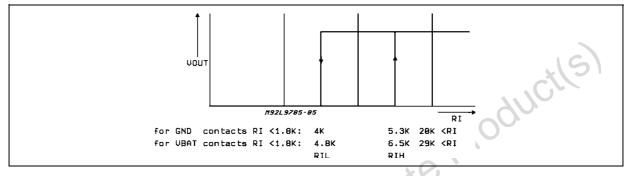
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The L9705 circuit compares the input current with the current through the internal reference resistor. The device is designed to work with an external input series resistor of $R_{IN1-8} = 1K\Omega$. With this input resistor the contact current, when the contact is closed and the device activated (EN =LOW) is:

$$I_{IN} = \frac{V_S - 2V}{1k\Omega} , \text{ for GND contacts, (1)}$$
$$I_{IN} = \frac{V_{BAT} + \Delta V_{BAT} - 2V}{1k\Omega} , \text{ fro } V_{BAT} \text{ contacts, (2)}$$

For this calculation the limit value of the V_S to V_{IN} and V_{IN} saturation voltage of 2V was considered so that the lowest limit value of I_{IN} is calculated in (1) and (2)





The function of the circuit can be demonstrated with the transfer characteristics, showing the output status as a function of the input resistor R_I , shown in figure 4. The input resistor is a sum of the R_{IN} and the contact resistance R_{CON} or R_{COFF} , for the closed contact:

 $R_I = R_{IN} + R_{CON}, (3)$

and for the open contact:

 $R_{I} = R_{IN} + R_{COFF}, \quad (4)$

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The output goes HIGH when the input resistance increases above $5.3K\Omega$ (GND contacts) or $6.5K\Omega$

 $(V_{BAT} \text{ contacts})$ and goes LOW, when the input resistance decreases below $4K\Omega$ (GND contacts) or $4.8K\Omega$ ($V_{BAT} \text{ contacts}$); these values are typical values for the switching thresholds. The limit values of $R_I = 1.8K\Omega$ (GND contacts) and $R_I = 1.8K\Omega$ ($V_{BAT} \text{ contacts}$) for LOW and $R_I = 20K\Omega$ (GND contacts) and $29K\Omega$ ($V_{BAT} \text{ contacts}$) for HIGH implies that a contact with $R_{CON} = 100\Omega$ (at $I_{IN} = 10$ mA) will be recognized as ON = LOW and a contact with $R_{COFF} = 19K\Omega$ (GND contacts) or $28K\Omega$ ($V_{BAT} \text{ contact}$) will be recognized as OFF = HIGH.

These limits are valid within the supply voltage range $6V \le V_S \le 16V$, the ground potential difference of $\Delta V_{GND} = 0.1V_S$, the battery voltage potential difference of $\Delta V_{BAT} < 0.1V_{BAT}$ and the variation of the reverse battery protection diode D1 voltage from 0.5V to 1V.

The internal clamping diodes at the contact monitoring inputs together with the external contacts series resistors R_{IN} allows to withstand the transients at the contact connection. The contact series resistor R_{IN} limits the input current at the transient.

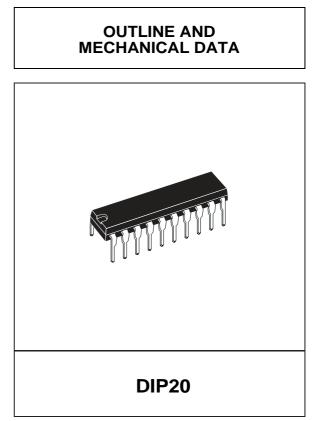
The dynamic behaviour of the circuit is defined with the times t_{do} and t_{dTS} . When the contact is open, the input capacitor C_{IN} must be charged through the resistor R_{IN} . In this case the total delay time tdo may be influenced also with the time constant $R_{IN}C_{IN}$.

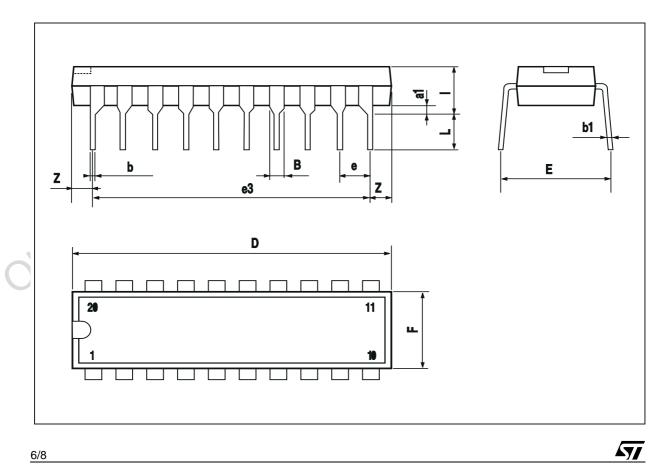
The delay time t_{dTS} , when disabling the device, is defined only with the internal circuitry. In both cases, output external capacitance less than 50pF is assumed, the internal output capacitance of the tristate buffers are less than 5pF.



L9705

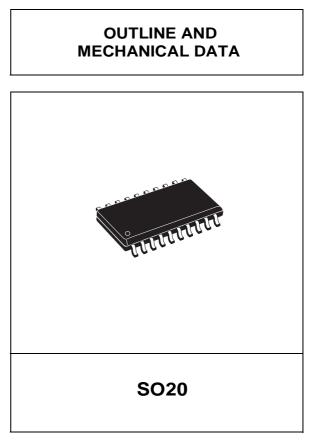
DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
a1	0.254			0.010			
В	1.39		1.65	0.055		0.065	
b		0.45			0.018		
b1		0.25			0.010		
D			25.4			1.000	
E		8.5			0.335		
е		2.54			0.100		
e3		22.86			0.900		
F			7.1			0.280	
I			3.93			0.155	
L		3.3			0.130		
z			1.34			0.053	

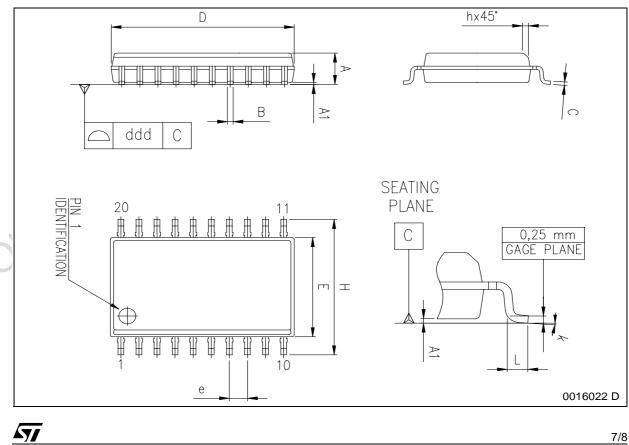




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DIM.	mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	2.35		2.65	0.093		0.104	
A1	0.10		0.30	0.004		0.012	
В	0.33		0.51	0.013		0.200	
С	0.23		0.32	0.009		0.013	
D ⁽¹⁾	12.60		13.00	0.496		0.512	
E	7.40		7.60	0.291		0.299	
е		1.27			0.050		
Н	10.0		10.65	0.394		0.419	
h	0.25		0.75	0.010		0.030	
L	0.40		1.27	0.016		0.050	
k	0° (min.), 8° (max.)						
ddd			0.10			0.004	
(1) "D" dimension does not include mold flash, protusions or gate burrs. Mold flash, protusions or gate burrs shall not exceed 0.15mm per side.							





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